

# WEST Search History

DATE: Wednesday, April 10, 2002

<u>Set Name</u> side by side	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u> result set
<i>DB=USPT,PGPB,JPAB,EPAB,DWPI,TDBD; PLUR=YES; OP=ADJ</i>			
L15	L2 and ((156/\$)!.CCLS.)	5	L15
L14	L12 and ((156/\$)!.CCLS.)	0	L14
L13	L10 and (resist or photoresist)	15	L13
L12	L10 and l1	0	L12
L11	L10 and l1	0	L11
L10	strip\$.ti. and ((solvent or water or rins\$) same laser)	98	L10
L9	L2 and ((solvent or water or rins\$) same laser)	75	L9
<i>DB=DWPI; PLUR=YES; OP=ADJ</i>			
L8	L1 and ((solvent or water or rins\$) same laser)	4	L8
L7	L2 and ((solvent or water or rins\$) same laser)	0	L7
L6	5763016	1	L6
<i>DB=USPT,PGPB,JPAB,EPAB,DWPI,TDBD; PLUR=YES; OP=ADJ</i>			
L5	L2 and (l1 same laser)	5	L5
L4	5037506	24	L4
L3	L2 and ((134/\$)!.CCLS.)	4	L3
L2	L1 and wafer and (uv or ultraviol\$ or radiation) and laser	224	L2
L1	so3 or "so.sub.3" or (sulfur trioxide) or (sulfur oxide)	55716	L1

END OF SEARCH HISTORY

**WEST**

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L4: Entry 21 of 24

File: USPT

Jul 13, 1993

US-PAT-NO: 5227001

DOCUMENT-IDENTIFIER: US 5227001 A

TITLE: Integrated dry-wet semiconductor layer removal apparatus and method

DATE-ISSUED: July 13, 1993

## INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Tamaki; Takio	Urawa			JPX
Chitre; Sanjeev R.	San Jose	CA		

US-CL-CURRENT: 156/345; 216/84

## ABSTRACT:

A system and process for removing a layer of a defined composition from a semiconductor wafer by performing at least one dry layer removal operation and at least one wet removal operation. A dry removal unit and a wet removal unit are disposed adjacent one another and robot mechanisms are provided to automatically transfer one wafer at a time through each unit in turn. The robot mechanisms are constructed to contact each wafer substantially at its edge in order to assure uniform treatment of both major surfaces of the wafer.

For stripping a resist layer from a wafer, the dry stripping operation can be performed first to remove a portion of the layer, after which the remainder of the layer is removed by the wet stripping operation. At the end of the wet stripping operation, the wafer is rinsed in water and used rinse water is monitored to determine at least one of its resistivity and total organic content in order to produce an indication that removal of undesired materials from the wafer surfaces has been completed. Subsequent to the wet treatment, the wafer is subjected to a cleaning with an aqueous mist on which ultrasonic vibrations are imposed.

19 Claims, 18 Drawing figures

Exemplary Claim Number: 1

Number of Drawing Sheets: 6